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**DOI**

[10.1109/JMEMS.2019.2943403](https://doi.org/10.1109/JMEMS.2019.2943403)

**Publication date**

2019

**Document Version**

Final published version

**Published in**

Journal of Microelectromechanical Systems

**Citation (APA)**

Sun, J., Sokolovskij, R., Iervolino, E., Liu, Z., Sarro, P. M., & Zhang, G. (2019). Suspended AlGaIn/GaN HEMT NO<sub>2</sub> Gas Sensor Integrated with Micro-heater. *Journal of Microelectromechanical Systems*, 28(6), 997-1004. Article 8856274. <https://doi.org/10.1109/JMEMS.2019.2943403>

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# Suspended AlGaIn/GaN HEMT NO<sub>2</sub> Gas Sensor Integrated With Micro-heater

Jianwen Sun<sup>ID</sup>, Robert Sokolovskij, Elina Iervolino, Zewen Liu, Pasqualina M. Sarro, *Fellow, IEEE*, and Guoqi Zhang, *Fellow, IEEE*

**Abstract**—We developed an AlGaIn/GaN high electron mobility transistor (HEMT) sensor with a tungsten trioxide (WO<sub>3</sub>) nano-film modified gate for nitrogen dioxide (NO<sub>2</sub>) detection. The device has a suspended circular membrane structure and an integrated micro-heater. The thermal characteristic of the Platinum (Pt) micro-heater and the HEMT self-heating are studied and modeled. A significant detection is observed for exposure to a low concentration of 100 ppb NO<sub>2</sub>/N<sub>2</sub> at ~300 °C. For a 1 ppm NO<sub>2</sub> gas, a high sensitivity of 1.1% with a response (recovery) time of 88 second (132 second) is obtained. The effects of relative humidity and temperature on the gas sensor response properties in air are also studied. Based on the excellent sensing performance and inherent advantages of low power consumption, the investigated sensor provides a viable alternative high performance NO<sub>2</sub> sensing applications. It is suitable for continuous environmental monitoring system or high temperature applications.

**Index Terms**—GaN, HEMT, micro-heater, WO<sub>3</sub>, NO<sub>2</sub> sensor.

## I. INTRODUCTION

RECENTLY, there have been growing concerns about environment pollution. The increasing demand for low power, compact, gas sensors for industrial and consumer applications drives the research of novel technologies towards miniaturization of the sensor without sacrificing sensitivity. Among polluting gases, nitrogen dioxide (NO<sub>2</sub>) is the one of the most harmful gases originating mainly from combustion of automobile exhaust (0.1~50 ppm) [1], furnaces, plants, etc. [2]

Manuscript received June 4, 2018; revised September 11, 2019; accepted September 17, 2019. Date of publication October 3, 2019; date of current version December 4, 2019. This work was supported by the Beijing Delft Institute of Intelligent Science and Technology. Subject Editor D. Devoe. (Corresponding authors: Pasqualina M. Sarro; Guoqi Zhang.)

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Digital Object Identifier 10.1109/JMEMS.2019.2943403

The concentration varies quite heavily with different application environments, which creates the need for wearable, low power, continuous environmental monitoring systems. Current sensors are not suited for continuous air quality monitoring due to high power, slow response, and low sensitivity (ppb level). In this paper, a novel design of AlGaIn/GaN HEMT NO<sub>2</sub> gas sensor integrated with a micro-heater is presented. AlGaIn/GaN heterojunctions exhibit great potential for high performance sensors development due to high carrier density two-dimensional electron gas (2DEG) at the interface introduced by the strong polarization effect, which is sensitive to the changes in surface potential [3]. Compared to AlGaIn/GaN Schottky diode sensors for nitric oxide (NO) [2], ammonia (NH<sub>3</sub>) [4], [5], nitrogen dioxide (NO<sub>2</sub>) [6], hydrogen (H<sub>2</sub>) [7], and acetone [8], AlGaIn/GaN HEMT sensors provide several advantages: Firstly, the current to be measured is larger than that in Schottky diodes, resulting in higher current changes and lower theoretical detection limits. Secondly, the sensitivity can be modulated and optimized by changing the gate bias. Finally, the 2DEG does not interact with the analytes but is sensitive to surface states. By functionalizing the gate area of a HEMT sensor for different analytes, such as enzymes, polyimides, or metals, sensitivity to H<sub>2</sub> [7], NO<sub>2</sub> [9], NH<sub>3</sub> [9], [10], methane (CH<sub>4</sub>) [11], pH [12], urea [13], glucose [14], chloride ion [15], heavy metal [16], and DNA [17] have been reported.

As for most of chemical sensing, as shown in numerous experimental works and theoretical considerations, the important parameters such as selectivity, sensitivity, and response time of gas sensors can be improved by increasing the surface temperature. To sustain elevated operating temperature, a heating element is often integrated into the sensor system.

As shown in figure 1, a voltage or current controlled MEMS micro-heater, with a suspended and thus thermally isolated structure, enables low power heating. The micro-heater and HEMT sensor area were defined as active area. From previous work [18], a SiO<sub>2</sub> layer with low thermal conductivity provides an effective thermal isolation between the active sensor area and the silicon frame for substantial reduction of power consumption, down to 5-100 mW, when the active area of sensor is heated to the desired operating temperature.

Here, for the first time, we have fabricated suspended AlGaIn/GaN HEMT sensors with WO<sub>3</sub> nano-film modified gate and integrated MEMS microheater as a sensor platform. The sensor comprises an AlGaIn/GaN membrane suspended within a silicon frame micromachined out of the silicon

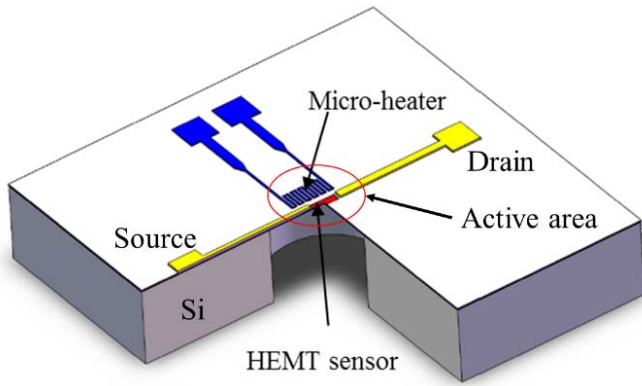


Fig. 1. Schematic of AlGaIn/GaN HEMT integrated with micro-heater.

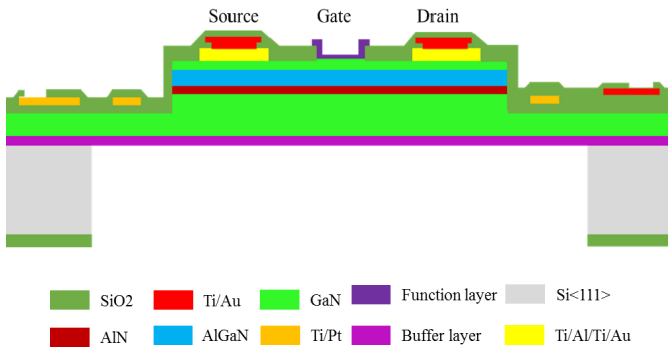


Fig. 2. Schematic cross-section of HEMT sensor structure.

wafer, and the following elements are over the membrane: a micro-heater which controls the temperature of the sensing layer, two  $\text{SiO}_2$  insulating layers, an HEMT sensor part and a  $\text{WO}_3$  nano-layer on top. The micro-heater performance and the AlGaIn/GaN self-heating on the membrane structure are studied for the first time. In addition, the temperature and relative humidity effects on AlGaIn/GaN sensor device are investigated and discussed. Finally, the response properties of HEMT sensor to  $\text{NO}_2$  gas with concentration of 0.1-40 ppm are presented. We conclude that the sensor concept that combines the HEMT sensor with a micro-heater can be applied to  $\text{NO}_2$  gases detection in consumer electronics and industrial applications.

## II. FUNDAMENTAL DESIGN AND FABRICATION PROCESSES

### A. Device Fabrication

Figure 2 presents a schematic drawing of the device cross-section. The HEMT sensor is placed together with the micro-heater surrounding the source/gate/drain area on a suspended membrane. The contact pads are on the thick silicon frame. The silicon substrate ( $400\ \mu\text{m}$ ) is backside etched away by deep reactive ion etching (DRIE) to form a circular membrane ( $650\ \mu\text{m}$  in diameter). The AlGaIn/GaN heterostructure was grown by Suzhou Nanowin Co. on a 2-inch silicon  $\langle 111 \rangle$  1 mm-thick wafers using Metal-organic Chemical Vapor Deposition (MOCVD). Starting from the substrate structure consisted of, a  $2\ \mu\text{m}$ -thick undoped GaN buffer layer, followed

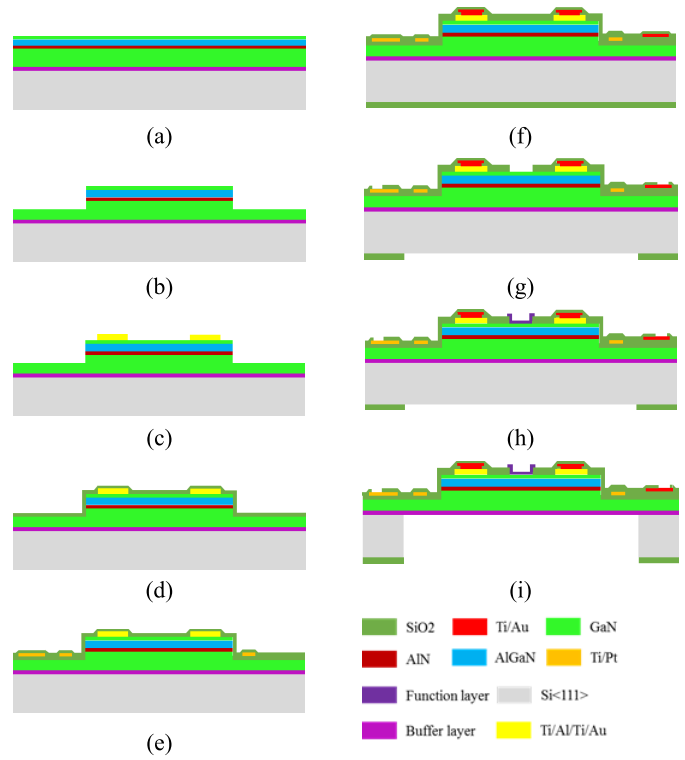


Fig. 3. Main steps for the fabrication of the suspended AlGaIn/GaN HEMT sensor integrated with micro-heater. (a) starting wafer with epitaxial layers; (b) mesa etching to define sensor area; (c) Ohmic contact deposition and annealing; (d) PECVD  $\text{SiO}_2$ ; (e) micro-heater deposition and passivation; (f) metal deposition and top/bottom passivation; (g) opening contact pads at the frontside and etching window at the backside; (h) functional material deposition; (i) substrate etching from the backside to form the suspended structure.

by a 1 nm-thick AlN interlayer, an undoped 25 nm-thick  $\text{Al}_{0.26}\text{Ga}_{0.74}\text{N}$  barrier layer, and a 3 nm-thick GaN epitaxial cap layer. The electron mobility was  $\sim 1500\ \text{cm}^2/\text{V}\cdot\text{s}$ , with a sheet electron density of  $\sim 1 \times 10^{13}\ \text{cm}^{-2}$ .

The fabrication process flow (Fig.3) started with a mesa etching using a chlorine/boron chloride ( $\text{Cl}_2/\text{BCl}_3$ ) plasma to define the sensor geometry. Then, Ti/Al/Ti/Au (20/110/40/50 nm) metal contacts were e-beam evaporated and patterned by lift-off technology. Rapid thermal annealing at  $870^\circ\text{C}$  for 45 seconds under  $\text{N}_2$  ambient in a RTP-500 system was conducted to make the contacts Ohmic and improve reliability at high temperature. 200-nm Silicon dioxide ( $\text{SiO}_2$ ) was then deposited by plasma-enhanced chemical vapor deposition (PECVD). A Ti/Pt (30/200 nm) metal layer was deposited by e-beam evaporation and patterned by lift-off to form the micro-heater, followed by a 200-nm PECVD  $\text{SiO}_2$  layer for isolation from the interconnect layer. The  $\text{SiO}_2$  was patterned in buffer oxide etch (BOE) solution and the thick metal interconnect formed using evaporated a Ti/Au (20/300 nm) layer stack. The topside of the wafer was covered by PECVD  $\text{SiO}_2$  layer and the backside was polished down to  $400\ \mu\text{m}$  and  $5\ \mu\text{m}$ -thick  $\text{SiO}_2$  layer was deposited as hard mask during the DRIE process to etch the silicon substrate. Then backside  $\text{SiO}_2$  was patterned by inductively coupled plasma (ICP) etching using AZ4620 photoresist as mask and the topside  $\text{SiO}_2$  layer was etched in BOE solution to form opening for the contact pads

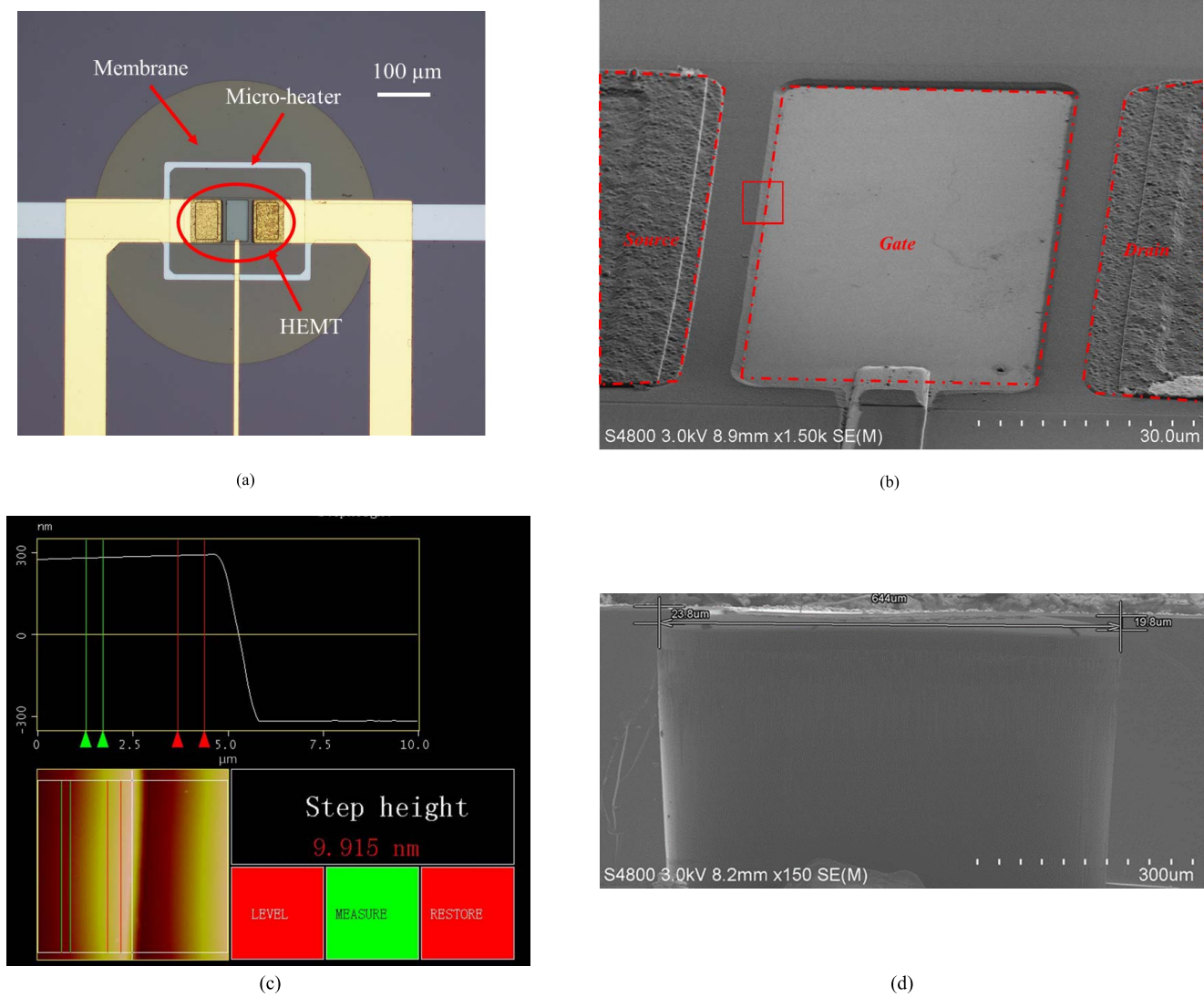


Fig. 4. The fabricated device: (a) optical image; (b) SEM image of HEMT sensor from 45° angle; (c) AFM image and step height measurement at red solid wireframe area of figure 4(b); (d) SEM image of the device cross section.

and gate windows. The WO<sub>3</sub> (10 nm) functional material layer was deposited on the gate area of 80 μm x 40 μm by physical vapor deposition (PVD). For comparison, the reference chip is without WO<sub>3</sub> layer deposition on gate area. The Silicon substrate is etched away below the active area in the final step. The microheater has a rectangle geometry around a central area of 230 μm x 290 μm, as showed in figure 4 (a). Figure 4 (b) and (d) show SEM images of the gate area from 45° angle and cross-sectional view of the fabricated sensor, respectively. Figure 4 (c) shows the AFM image and step height measurement of 10 nm WO<sub>3</sub> layer.

After dicing, the chips were wire-bonded to a prototype with ceramic quad flat no-lead (CQFN) package with size of 4 mm x 4 mm (Fig. 5). This sensor package is designed to eliminate the effect of gas flow by a perforated lid.

### B. Measurement Set Up

For gas testing experiments, the HEMT sensors were placed in a stainless steel chamber (20 mL) and connected to a

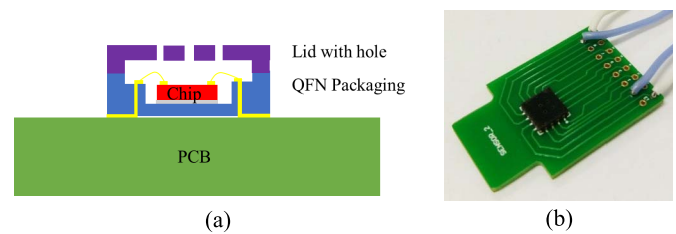


Fig. 5. (a) the schematic diagram of a gas sensor package; (b) the photograph of a packaged sensor on test PCB.

Keithley 2700 and a power source. Gas sources of pure N<sub>2</sub> and varying concentration of NO<sub>2</sub> were inserted in the testing chamber based on dynamic gas distribution instrument at atmospheric pressure. The gas flow rate was controlled at 100 sccm and the concentration of NO<sub>2</sub> in N<sub>2</sub> was varied from 100 ppb to 50 ppm at ambient temperature.



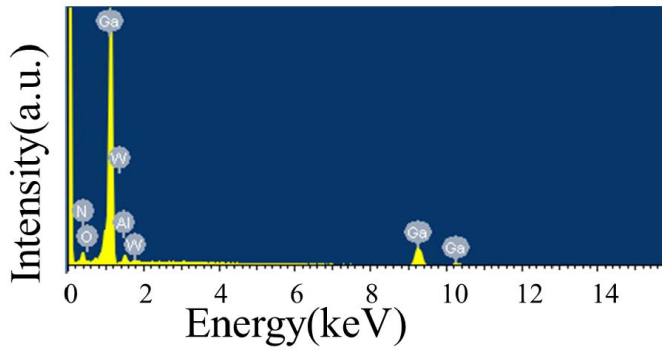


Fig. 6. EDS spectrum of the gate surface of the HEMT sensor.

### III. RESULTS AND DISCUSSION

The energy dispersive spectrum (EDS) of the device gate area surface is reported in figure 6. The corresponding peaks of Ga, W, N, Al, O elements are observed. Clearly, the deposition of  $\text{WO}_3$  on the gate surface by magnetron sputtering is confirmed.

#### A. Micro-Heater Calibration and Thermal Characterization

Before the heater is used as heating element, it is necessary to perform a calibration for extracting the temperature of active area, which is between source and gate. The sample is placed in an oven and the temperature was varied from 303.15 K up to 353.15 K and the resistance versus temperature curve has been recorded. Low current values are supplied to the Pt heater element to prevent self-heating of the heater itself. The temperature dependence of the resistivity is well described by the following linear equation:

$$\rho_H(T) = \rho_0 [1 + \alpha (T - T_0)] \quad (1)$$

where  $\rho_H$  and  $\rho_0$  are, respectively, the heater resistivity at temperature  $T$  and at ambient temperature  $T_0$ ;  $\alpha$  is the thermal coefficient of resistance (TCR). The measured TCR of the heater is equal to 3861 ppm/K with a deviation of 10 ppm/K according to the RTD standard [19].

However, the self-heating effect of the AlGaIn/GaN HEMT device also causes a local increase in crystal temperature due to the dissipated Joule electric power. The combined thermal characteristic of the Pt micro-heater and the HEMT self-heating at ambient temperature is shown in Figure 7. The surface temperature can be measured by infrared radiation (IR) thermal camera or extracted by the resistance change of the micro-heater at ambient temperature, showing a linear growth with increasing the drain-source voltage,  $V_{DS}$ . Figure 7 shows the max temperature distribution on the gate surface when changing the voltage of drain-source,  $V_{DS}$ , and micro-heater,  $V_H$ . Figure 8 shows measured heating power consumption of micro-heater and temperature versus microheater voltage at  $V_{DS} = 5$  V. As adding the voltage of micro-heater,  $V_H$ , the max temperature of gate surface will nonlinear grow. When the voltage of micro-heater is  $V_H = 4$  V and  $V_H = 3$  V, the max gate surface temperature is about 297.87 °C and 135 °C. In fact, the power of sensor is about 200 mW when the

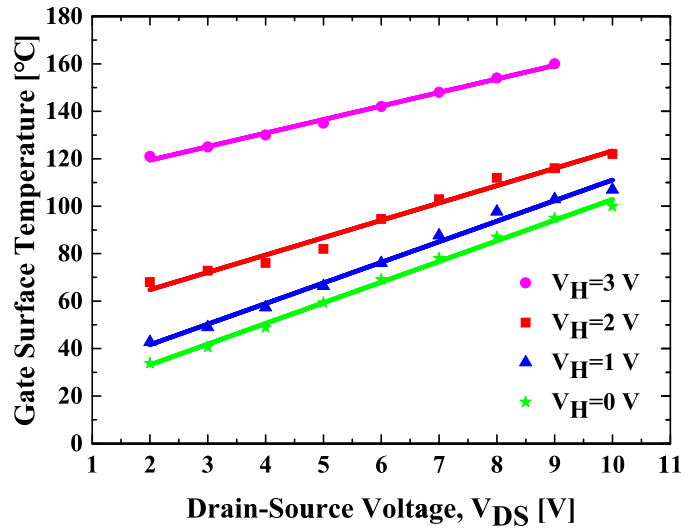


Fig. 7. Combined heating characteristic of the Pt micro-heater and HEMT self-heating at ambient temperature of 298.15 K for voltage of micro-heater,  $V_H = 0$  V to 3 V and  $V_{DS} = 2$  V to 10 V with 1 V increments.

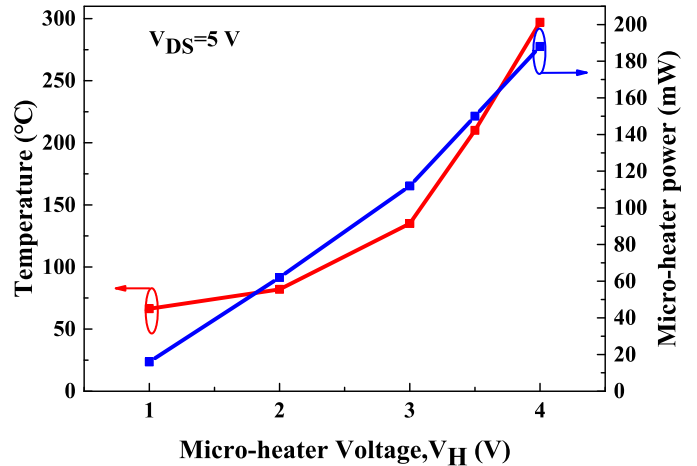


Fig. 8. Measured heating power consumption of micro-heater and temperature versus microheater voltage at  $V_{DS} = 5$  V.

operating temperature is about 300 °C. The reasons of a little high power maybe as following: one is the residual Si around the membrane during the DRIE process; another one is the ceramic package with high thermal conductivity coefficient resulting in increased the power consumption. The power of the sensor will be optimized in the next phase. To further improve heating efficiency, a larger size membrane and cycle heating [10] can be utilized.

#### B. Temperature and Humidity Measurement

The AlGaIn/GaN HEMT devices were tested versus ambient temperature and humidity in the 263 K to 353 K range, with 10 K steps, and the 5% RH to 90% RH range. The gate voltage of the HEMT device was left floating and  $V_{DS}$  varied from 0V to 20 V. As shown in figure 9, the saturated current has a little drop with raising  $V_{DS}$  due to the thermal and lattice scattering of the 2DEG. And the  $I_{DS}$  decreases remarkably between 263 K and 353 K at 20% RH. The saturated current

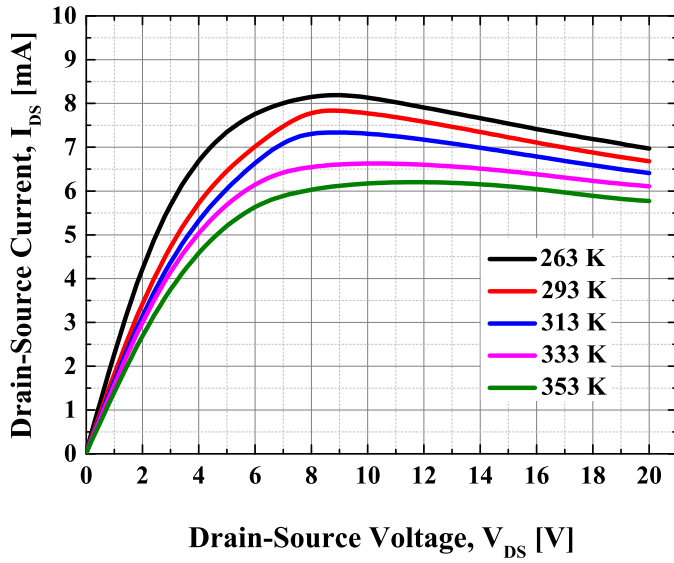


Fig. 9. I-V characteristics of HEMT sensor under variable ambient temperature at 20% relative humidity.

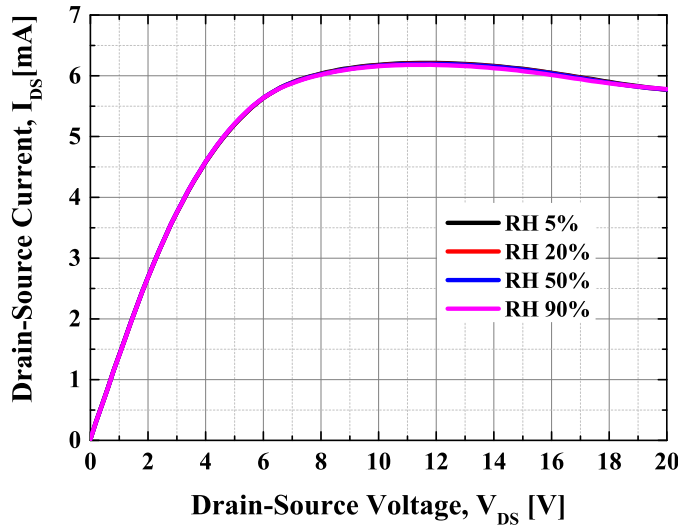


Fig. 10. I-V characteristics of HEMT sensor under different relative humidity at 353.15 K.

temperature coefficient is  $-0.63 \text{ mA/mm} \cdot \text{K}$ , which is in agreement with results from literature [20]. Figure 10 indicates that the relative humidity has no significant effect on the I-V characteristics of HEMT at 353.15 K. The humidity effect at different temperatures is shown in Figure 11. The  $I_{DS}$  decreases upon increasing the relative humidity from 5% to 90% at low temperature. However, the effect of relative humidity on  $I_{DS}$  becomes insignificant with increasing ambient temperature. Of course, the temperature influence should be avoided during measurement. In order to eliminate the temperature interference, a differential method (including a second structure with the same geometry but not exposed to gas/humidity in one chip) can be a suitable solution.

### C. Gas Sensing Measurement

The gas sensors were placed in the testing chamber and heated to 571 K while exposed to 0.1-40 ppm NO<sub>2</sub>

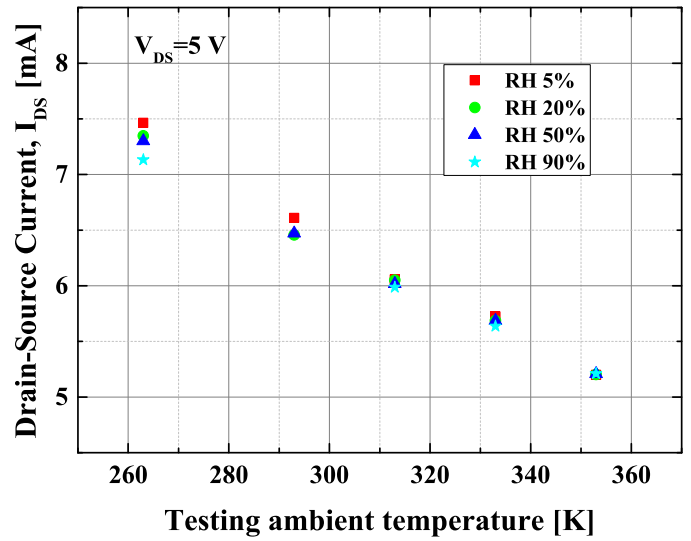


Fig. 11. Temperature and relative humidity effect on the  $I_{DS}$  of HEMT sensor at  $V_{DS} = 5 \text{ V}$ .

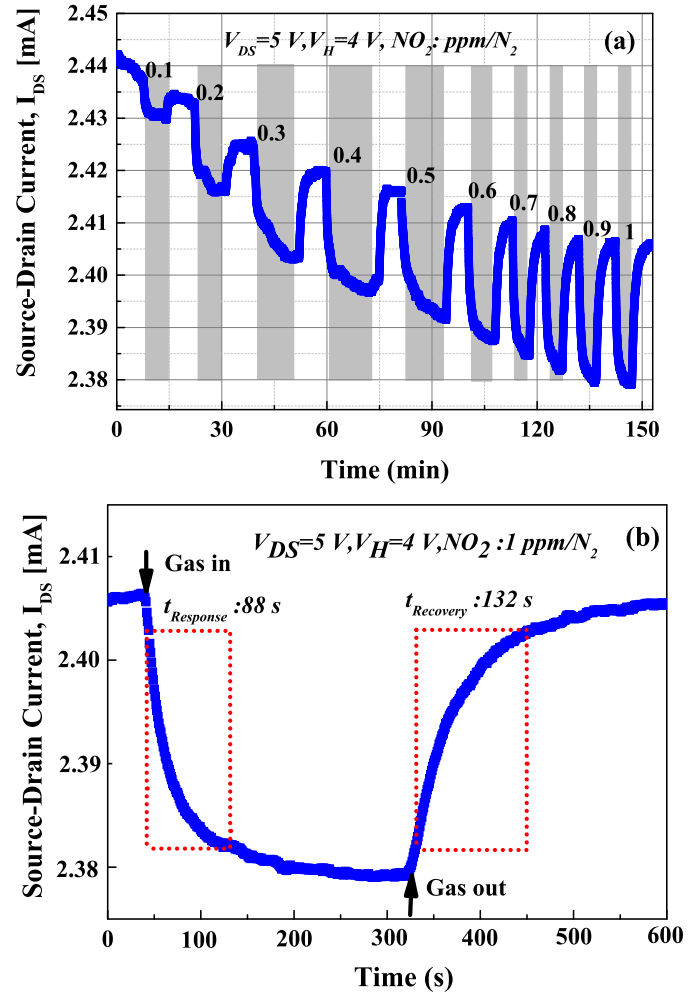


Fig. 12. Transient response of AlGaIn/GaN HEMT sensor to NO<sub>2</sub> gas concentrations at  $\sim 300^\circ \text{C}$  (a) 0.1-1 ppm. (b) Enlarged part of the response curve of 1 ppm.

gas in pure N<sub>2</sub>. Figure 12 (a) presents that the transient response of AlGaIn/GaN sensor for 0.1-1 ppm at the operating bias of  $V_{DS} = 5 \text{ V}$  and  $V_H = 4 \text{ V}$ . A clear effect is

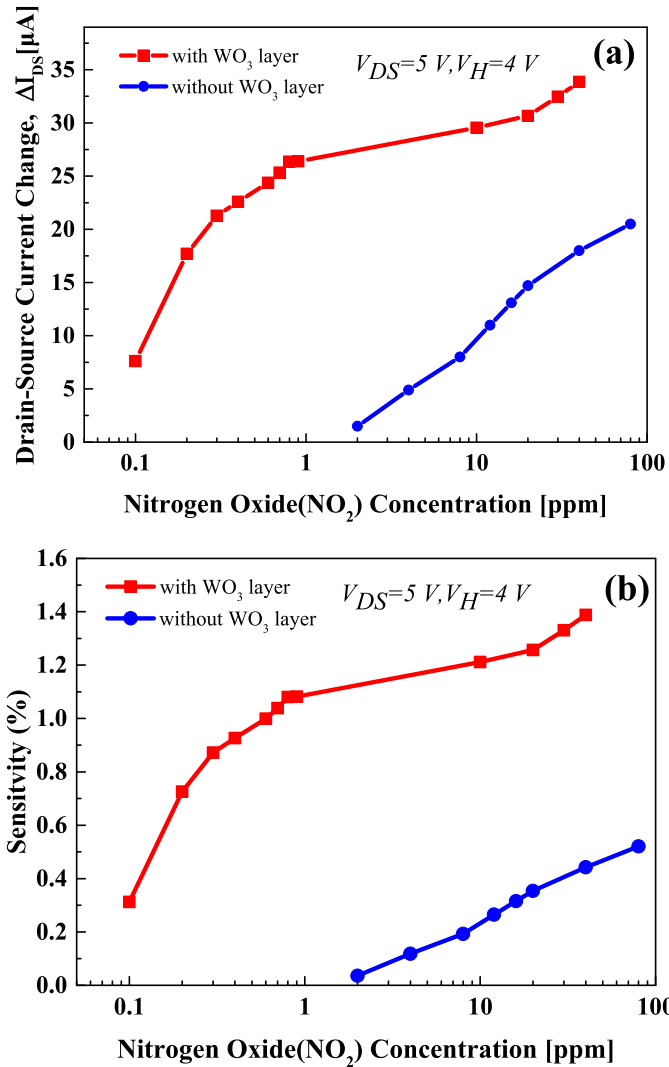


Fig. 13. Gas concentration dependent sensing properties of HEMT sensor for 0.1-80 ppm  $\text{NO}_2$  gas at  $\sim 300^\circ\text{C}$ .

observed under a low concentration of 100 ppb  $\text{NO}_2/\text{N}_2$  at  $\sim 300^\circ$ . Figure 12 (b) shows the enlarged parts of data in figure 12 (a) measured at a  $\text{NO}_2$  concentration of 1 ppm. To qualify a sensor to be efficient, response time and recovery time are crucial to be determined. Response time ( $t_{\text{Response}}$ ) and recovery time ( $t_{\text{Recovery}}$ ) were defined as the time required for the drain current to change/return from 10% to 90 % of its saturated response value to  $\text{NO}_2$  gas. And as shown in Figure 13, the current change values ( $\Delta I$ ) and sensitivity ( $S = \Delta I/I$ ) toward  $\text{NO}_2$  gas increase after  $\text{WO}_3$  layer deposition. At the concentration of 10 ppm,  $\Delta I$  and  $S$  were found to increase from  $9\text{ }\mu\text{A}$  and  $0.25\%$  to  $29\text{ }\mu\text{A}$  and  $1.21\%$ , respectively. And the limit of sensor detection also be improved from 2 ppm to 100 ppb. Figure 14 characterizes the response time and recovery time as function of  $\text{NO}_2$  concentration with  $\text{WO}_3$  layer and without  $\text{WO}_3$  layer. The response time of sensor with  $\text{WO}_3$  layer is improved from 423 second to 91 second at 10 ppm. However, the recovery time of device without  $\text{WO}_3$  layer are faster. The possible reason is that the AlGaIn surface is easy for  $\text{NO}_2$  molecule desorption. At the concentration

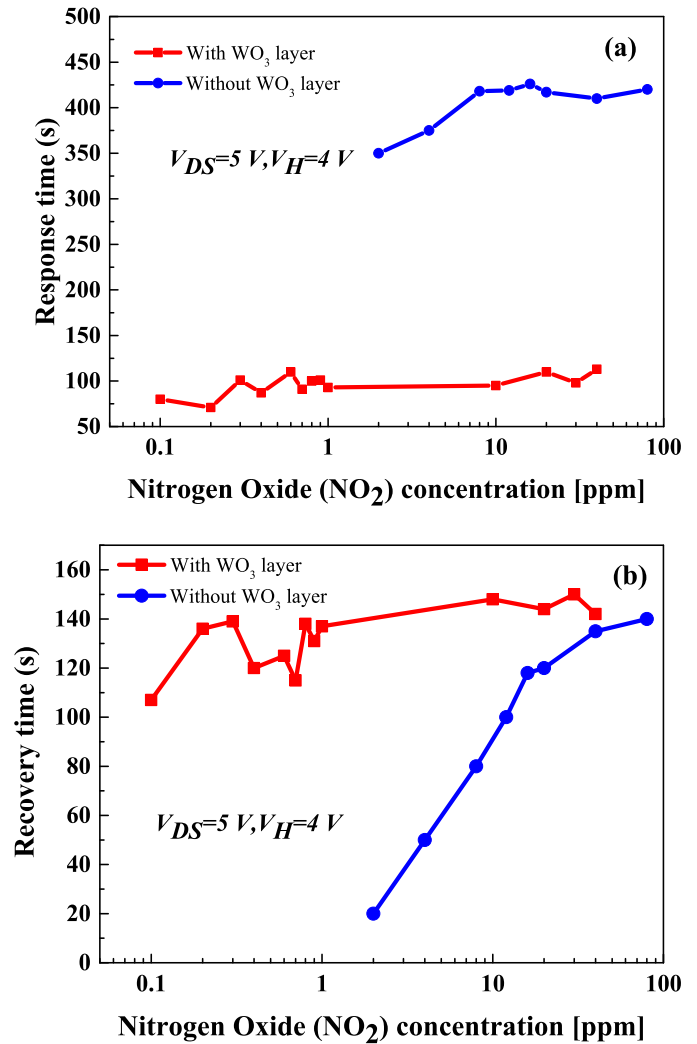


Fig. 14. Response time (b) and recovery time (c) versus  $\text{NO}_2$  concentration.

of 1 ppm,  $\Delta I$  and  $S$  were found to be  $26\text{ }\mu\text{A}$  and  $1.1\%$  with a response and recovery time of 88 second and 132 second, respectively. The response times could be further reduced with a shorter distance between the gas cylinder and the sensor. The effect of the working temperature, known to have great influence on the sensitivity of gas sensor, was studied as well. The current change and sensitivity as a function of micro-heater voltage are plotted in Figure 15. The sensitivity of sensor exposed to 10 ppm  $\text{NO}_2$  at  $V_H = 3\text{ V}$  ( $135^\circ$ ),  $V_H = 3.5\text{ V}$  ( $210^\circ$ ) and  $V_H = 4\text{ V}$  ( $300^\circ$ ) are  $0.29\%$ ,  $0.9\%$  and  $1.4\%$ , respectively. The sensing properties are significantly enhanced with increasing micro-heater voltage (temperature). Nano  $\text{WO}_3$  gate AlGaIn/GaN HEMT sensors have shown a great potential to detect low  $\text{NO}_2$  concentration with a fast response time.

#### D. Sensing Mechanism

Several potential sensing mechanisms have been reported based on adsorption on surface of catalytic metal dissociate and release electrons [9], [21], [22] When the sensor are exposed to  $\text{NO}_2$  gas, chemisorption reaction on the  $\text{WO}_3$



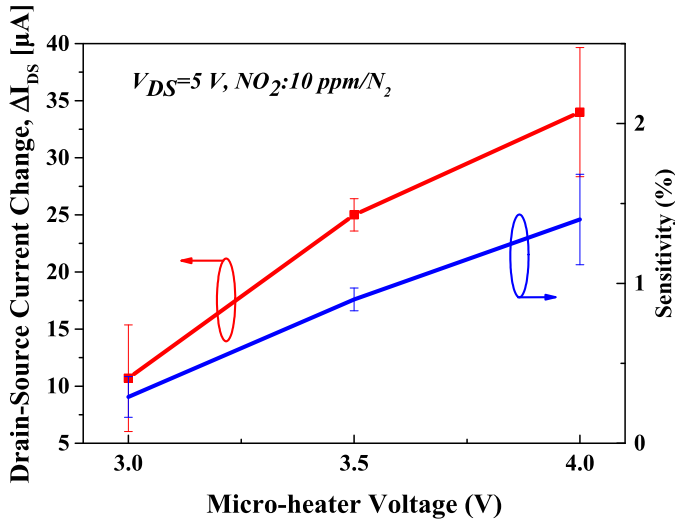
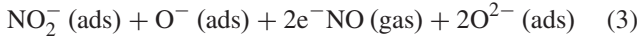


Fig. 15. Current change and sensitivity of sensor with WO<sub>3</sub> layer to 10 ppm NO<sub>2</sub> at different micro-heater voltages (temperature).

surface results in gas ions (negatively charged for NO<sub>2</sub>) that rapidly diffuse at the surface. NO<sub>2</sub> gas adsorb directly on the surface of WO<sub>3</sub> layer as well as reacts with adsorbed O<sup>-</sup> ions according to the following reaction [23]



On the other hand, the surface states would be altered by the polar NO<sub>2</sub> molecules, which would manipulate the 2DEG concentration. Therefore, the surface potential of the WO<sub>3</sub> and AlGaIn are changed, resulting in the variation of drain current of the HEMT device. The changed surface potential can mathematically be represented by the Helmholtz model

$$\Delta V = \frac{N_S p (\cos \theta)}{\epsilon \epsilon_0} \quad (4)$$

where  $p$  is the dipole moment,  $N_S$  is the dipole density per unit area,  $\theta$  is the angle between the dipole and the normal surface,  $\epsilon$  is the relative permittivity of the material, and  $\epsilon_0$  is the permittivity of free space. The surface potential is major affected by the value of  $p/\epsilon$  of the polar molecules.

#### IV. CONCLUSIONS

In conclusion, nano-film WO<sub>3</sub> gate AlGaIn/GaN HEMT sensors integrated with micro-heater on suspended membrane have been microfabricated and characterized. The combined effect of micro-heater heating and self-heating on membrane has been studied first time. Significant detection is observed under a low concentration of 100 ppb NO<sub>2</sub>/N<sub>2</sub> at ~300 °. As exposed to a 1 ppm NO<sub>2</sub> gas, a high sensing sensitivity of 1.1% with a response (recovery) time of 88 second (132 second) is obtained. The sensor shows is not affected under high relative humidity ambient while the temperature influence need be avoided. Based on the excellent sensing performance and inherent advantages of low power consumption, the HEMT

sensor combined nano-film WO<sub>3</sub> functional gate and micro-heater provides an attractive alternative for high performance NO<sub>2</sub> sensing applications.

#### ACKNOWLEDGMENT

Fabio Santagata is acknowledged for his kind help during the design and processes. The authors would like to thank Prof. Junxi Wang and the staff of the Institute of Semiconductor, Chinese Academy of Sciences for their assistance in device fabrication, and Xueping Guo from Institute of Microelectronic of Chinese Academy of Sciences for the packaging.

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